

S3CC9ED

Advanced Information
Publication Number 00-S3-CC9ED
March 2002 (Rev.0)

CMOS Microcontroller for Smart Card Applications

OVERVIEW

The **S3CC9ED** single-chip CMOS micro-controller is designed for low voltage smart card applications and is fabricated using an advanced 0.18-micron CMOS process. Its fast and reliable 16-bit CPU is based on the smart card-purpose CalmRISC16 processor.

FEATURES

CPU

16-bit CalmRISC16 CPU core

Memory Allocation

- 384k Bytes ROM
- 128k Bytes EEPROM
- 8k Bytes static RAM
- Memory Protection Unit

EEPROM Operations

- 1 to 128 bytes EEPROM erase/write operations
- 2.0 ms fast erase/write time
- 500K erase/write cycles (minimum)
- 50 years data retention (minimum)

Data Security

- 128 bytes write protected security area
- 128 bytes of non erasable EEPROM
- Reset operations are selective if abnormal condition is detected.

DES/T-DES

- Built-in hardware DES/T-DES
- circuit for prevent SPA/DPA

Interrupts

 Four interrupt sources and vectors (FIQ, IRQ, SWI)

Clock sources

• External: 1MHz – 5MHz

Internal variable clock : 10MHz+-10%(Vdd=5V)

Serial I/O interface

 Hardware UART for handing serial interface in accordance with ISO 7816 communication protocols

Random Number Generator

- One 16-bit random number generator
- Start and stop control

Memory Protection Unit

- Read/write access controllable
- Base/Limit region registers: 8 sets
- Configurable range: 4-Mbyte areas with 128byte resolution.
- · All the controls can be done at privilege mode

Bus scrambling

- RAM BUS scrambling with random number
- EEPROM BUS scrambling with user defined seed

Security detector

Many kind of security detectors

Timers

- 16-bit timer with 8 bit prescaler
- One 20-bit watchdog timer

Operating Characteristics

- Single power supply: 1.62 to 5.5 V
- Operating frequency: 1 to 5 MHz
- Operating temperature: -25 °C to +85 °C

Package

8-pin COB (conforms to ISO standard 7816)



S3CC9ED ADVANCED INFORMATION

BLOCK DIAGRAM

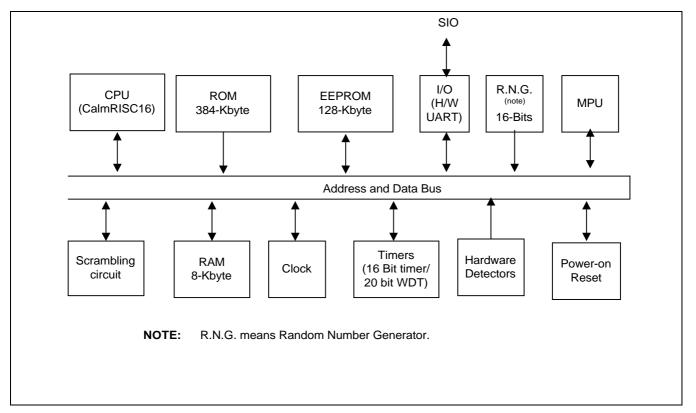


Figure 1. Block Diagram

ELECTRICAL DATA

$$(T_A = -25 \,^{\circ}C \text{ to } + 85 \,^{\circ}C, V_{DD} = 1.62 \,\text{V} \text{ to } 5.5 \,\text{V})$$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Supply current	I _{DD1}	F _{CLK} = 5 MHz, 5.5 V	_	-	10	mA
		F _{CLK} = 4 MHz, 3.3 V	_	_	6	
Stop Current	I _{DD2}	F _{CLK} = 1 MHz, 5.5 V	_	_	200	μΑ
	I _{DD3}	F _{CLK} = GND, 5.5 V	-	_	100	μΑ

Table 1. Electrical Characteristics